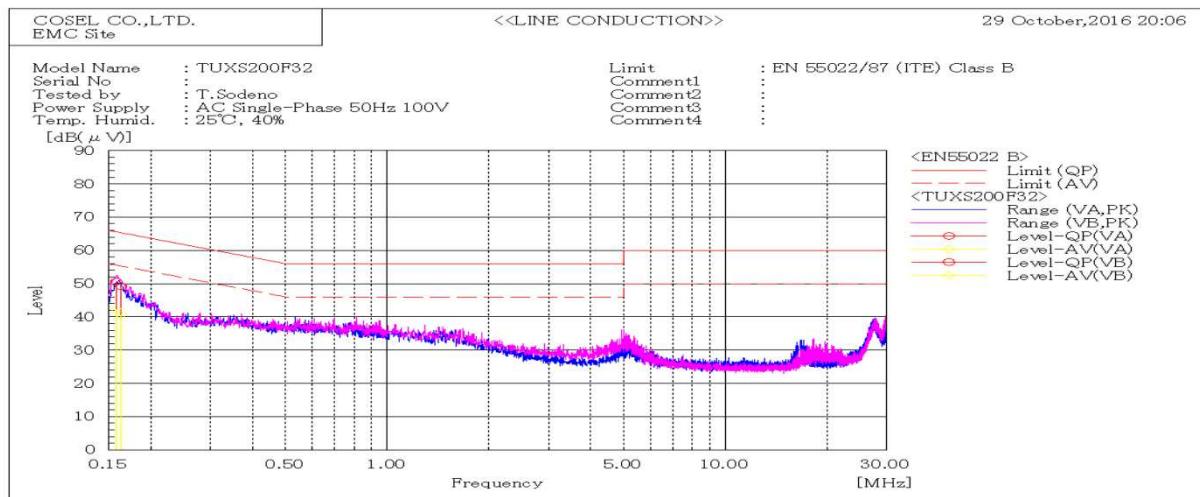
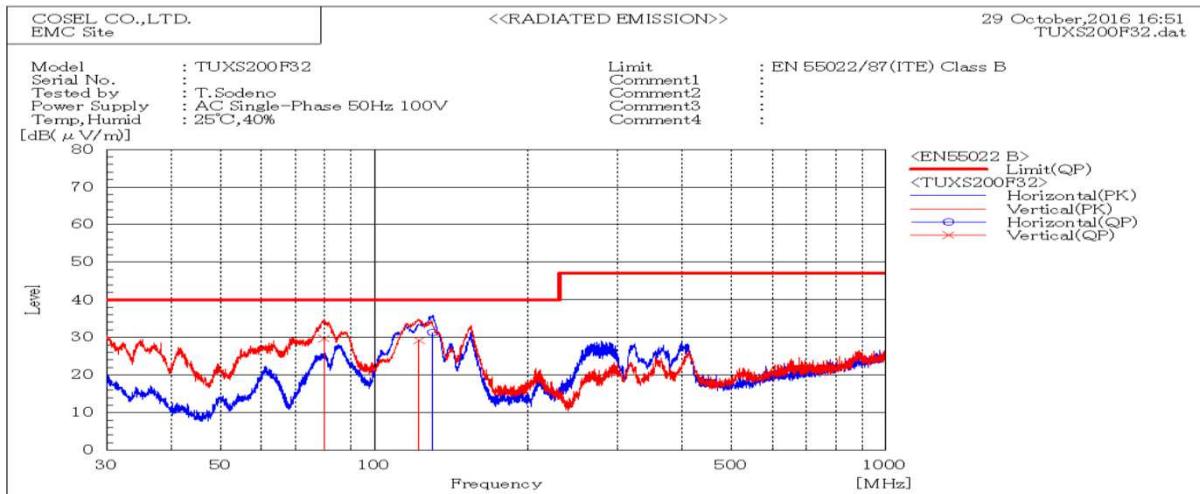


DATA SHEET

Date	31-Oct-16		
Model	TUXS200F32	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	T.Sodeno



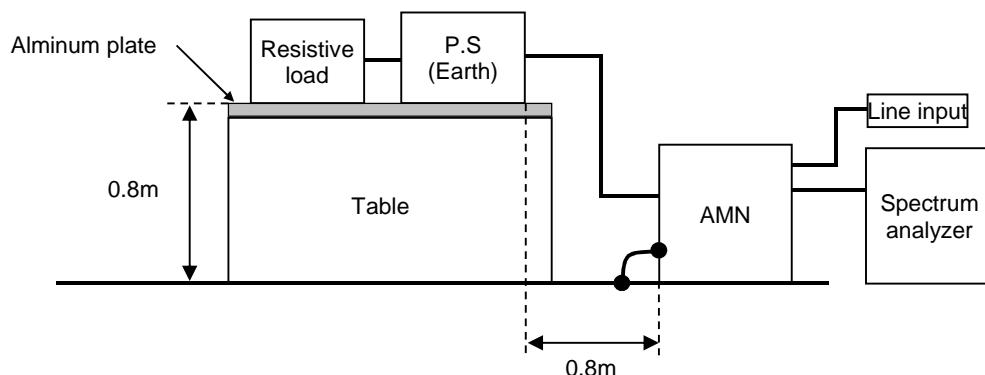
Frequency MHz	Line Phase	Level dB(μV)		Limit dB(μV)		Margin dB		Pass/Fail
		QP	AV	QP	AV	QP	AV	
0.15757	VB	50.6	42.3	65.6	55.6	15	13.3	Pass
0.16326	VA	49.2	40.6	65.3	55.3	16.1	14.7	Pass



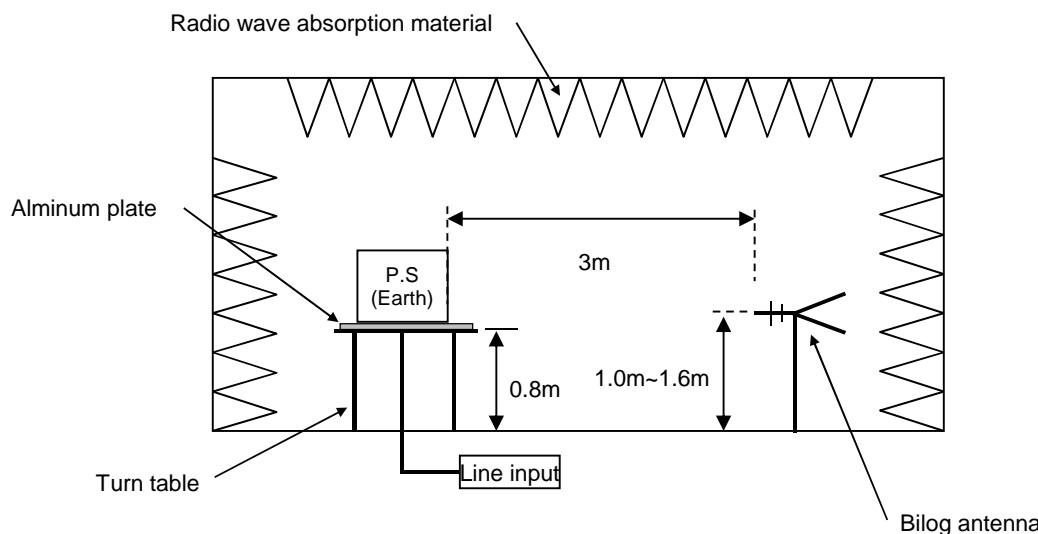
Frequency MHz	Polarization	Stability	Reading dB(uV)	Limit dB(uV/m)	Margin dB(uV/m)	Pass/Fail	Height cm	Angle deg
			QP	QP	QP			
79.595	V	Stable	29.8	40.0	10.2	Pass	110	253
122.114	V	Stable	29.2	40.0	10.8	Pass	100	279
130.006	H	Stable	31.3	40.0	8.7	Pass	153	194

DATA SHEET		Date	31-Oct-16
Model	Circuit used for measurement	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	T.Sodeno

1. Line conduction



2. Radiated emission



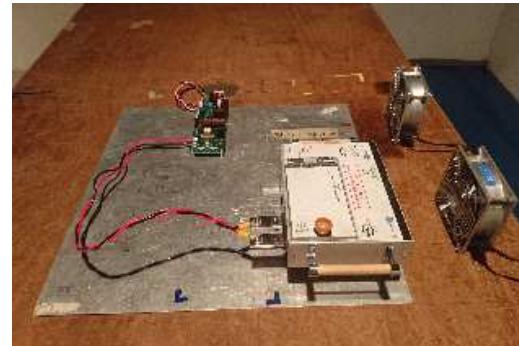
Test: EMI
Model Name:TUXS200F32

○ Photographs of Test Set-Up

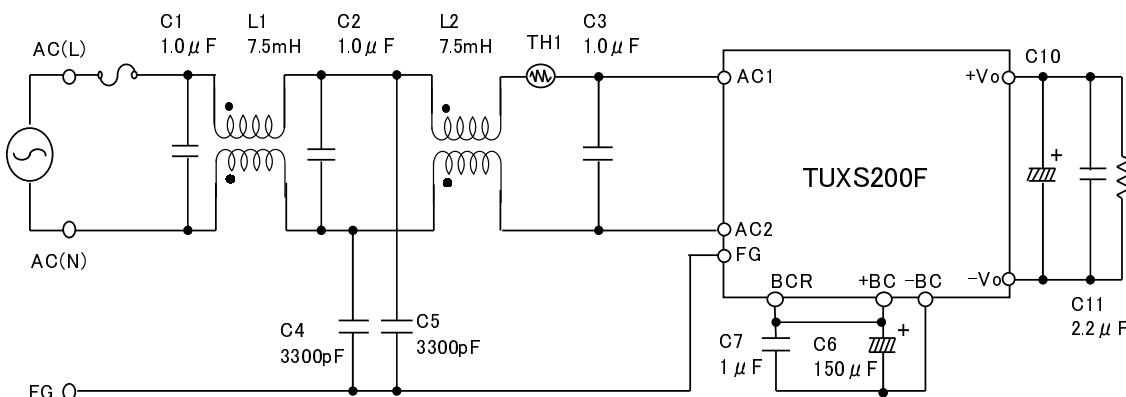
LINE CONDUCTION



RADIATED EMISSION



○ Test circuit



- L1,L2 : SCR22-060-1R0A075JH(NEC TOKIN)
- TH1 : 12D2-11LC(SEMITEC)
- C1,C2,C3 : LE105-MX(OKAYA)
- C4,C5 : DE1E3KX332M(MURATA)
- C6 : EKXJ421ELL151MM50S(Nippon Chemi-con)
- C7 : AFS450V105K(OKAYA)
- C10 : PCR1H181MCL1GS(NICHICON) × 3
- C11 : GRM31CR72A225K(MURATA)